

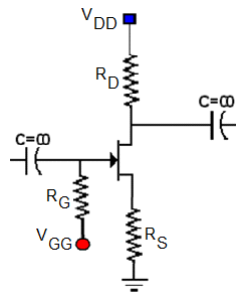
Electronics

J-FET biasing

Problem 1.- The J-FET based circuit shown below has the following specifications:

$$I_{DSS} = 12 \text{ mA}, V_P = -6\text{V}, R_G = 1 \text{ M}\Omega, V_{GG} = -3\text{V}, R_D = 3.3 \text{ k}\Omega \text{ y } R_S = 820\Omega$$

- 1) Find the operating point of the transistor assuming it is in the active region.
- 2) Calculate the minimum value of V_{DD} to be in the active region.



Solution.- If the transistor is in the active region, the drain current is:

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

But because of the way it is biased, we notice that $V_{GS} = -3\text{V} - 820\Omega I_D$

That we can replace in the equation above to get:

$$I_D = 12\text{mA} \left(1 - \frac{-3\text{V} - 820\Omega I_D}{-6} \right)^2$$

Solving for I_D

$$36I_D = 12\text{mA} (3\text{V} - 0.82\text{k}\Omega I_D)^2$$

$$I_D = 1.27\text{mA}$$

$$I_D = 10.5\text{mA}$$

We accept the first solution as correct. The other (10.3mA) would make V_{GS} greater than V_P .

With this current we can now calculate the values at the Q point:

$$V_S = 1.27\text{mA} \times 0.82\text{k}\Omega = 1.04\text{V}$$

$$V_{GS} = V_G - V_S = -3\text{V} - 1.04\text{V} = -4.04\text{V}$$

The voltage drop in the drain resistor is:

$$V_{RD} = 1.27\text{mA} \times 3.3\text{k}\Omega = 4.20\text{V}$$

The minimum drain-source voltage is given by the relation between V_P and I_{DSS} :

$$V_{DS(\min)} = \frac{|V_P|}{I_{DSS}} I_D = \frac{6}{12} (1.27) = 0.63\text{V}$$

So the minimum source voltage has to be:

$$V_{DD(\min)} = 4.20\text{V} + 0.63\text{V} + 1.04\text{V} = 5.89\text{V}$$

With the understanding that a higher voltage would be better.